

# 4V Drive Nch MOSFET

## RSJ10HN06

### ● Structure

Silicon N-channel MOSFET

### ● Features

- 1) Low on-resistance.
- 2) Built-in G-S Protection Diode.
- 3) High power Package

### ● Application

Switching

### ● Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	1000
RSJ10HN06		○

### ● Absolute maximum ratings (T<sub>a</sub> = 25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage	V <sub>DSS</sub>	60	V	
Gate-source voltage	V <sub>GSS</sub>	±20	V	
Drain current	Continuous	I <sub>D</sub> *3	±100	A
	Pulsed	I <sub>DP</sub> *1	±200	A
Source current (Body Diode)	Continuous	I <sub>S</sub> *3	100	A
	Pulsed	I <sub>SP</sub> *1	200	A
Power dissipation	P <sub>D</sub> *2	100	W	
Channel temperature	T <sub>ch</sub>	150	°C	
Range of storage temperature	T <sub>stg</sub>	-55 to +150	°C	

\*1 P<sub>w</sub>≤10μs, Duty cycle≤1%

\*2 T<sub>c</sub>=25°C

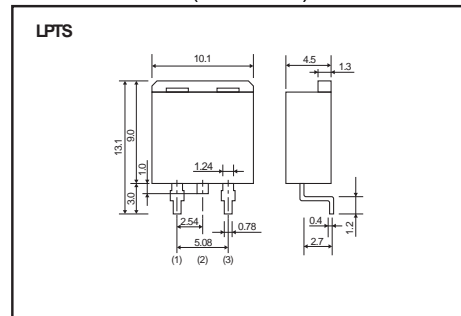
\*3 Limited only by maximum channel temperature allowed.

### ● Thermal resistance

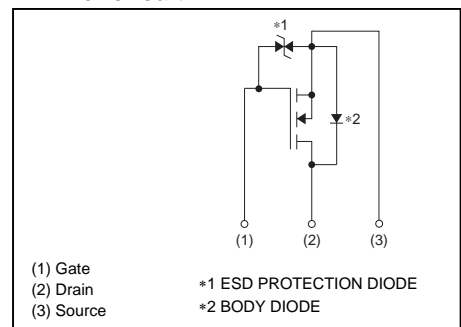
Parameter	Symbol	Limits	Unit
Channel to Case	R <sub>th (ch-c)</sub> *	1.25	°C / W

\* T<sub>c</sub>=25°C

### ● Dimensions (Unit : mm)



### ● Inner circuit



**●Electrical characteristics (T<sub>a</sub> = 25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I <sub>GSS</sub>	-	-	±10	μA	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	60	-	-	V	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	-	-	1	μA	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS(th)</sub>	1.0	-	2.5	V	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA
Static drain-source on-state resistance	R <sub>DS(on)</sub> *	-	3.0	4.2	mΩ	I <sub>D</sub> =50A, V <sub>GS</sub> =10V
		-	3.5	4.9		I <sub>D</sub> =50A, V <sub>GS</sub> =4V
Forward transfer admittance	Y <sub>fs</sub>  *	60	-	-	S	V <sub>DS</sub> =10V, I <sub>D</sub> =50A
Input capacitance	C <sub>iss</sub>	-	11000	-	pF	V <sub>DS</sub> =10V
Output capacitance	C <sub>oss</sub>	-	2000	-	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	C <sub>rss</sub>	-	1050	-	pF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	-	50	-	ns	V <sub>DD</sub> ≒30V, I <sub>D</sub> =50A
Rise time	t <sub>r</sub> *	-	470	-	ns	V <sub>GS</sub> =10V
Turn-off delay time	t <sub>d(off)</sub> *	-	420	-	ns	R <sub>L</sub> =0.6Ω
Fall time	t <sub>f</sub> *	-	710	-	ns	R <sub>G</sub> =10Ω
Total gate charge	Q <sub>g</sub> *	-	202	-	nC	V <sub>DD</sub> ≒30V, I <sub>D</sub> =50A
Gate-source charge	Q <sub>gs</sub> *	-	35	-	nC	V <sub>GS</sub> =10V
Gate-drain charge	Q <sub>gd</sub> *	-	42	-	nC	

\*Pulsed

**●Body diode characteristics (Source-Drain)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward Voltage	V <sub>SD</sub> *	-	-	1.5	V	I <sub>s</sub> =100A, V <sub>GS</sub> =0V

\*Pulsed

●Electrical characteristic curves (Ta=25°C)

Fig.1 Typical Output Characteristics ( I )

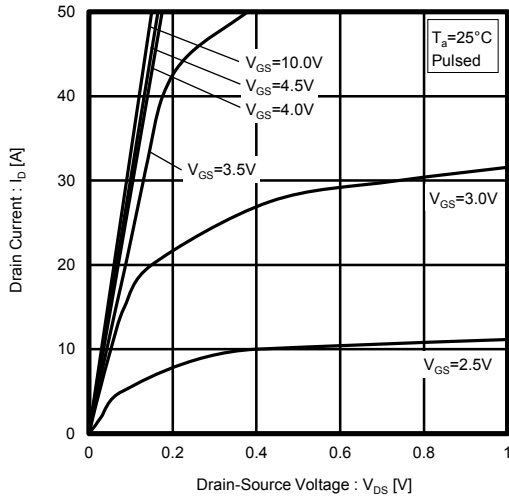


Fig.2 Typical Output Characteristics ( II )

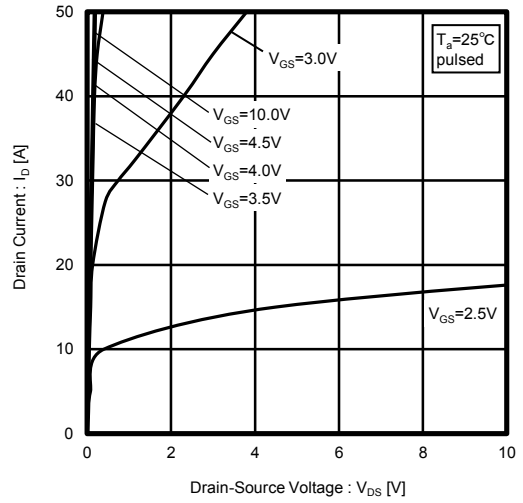


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

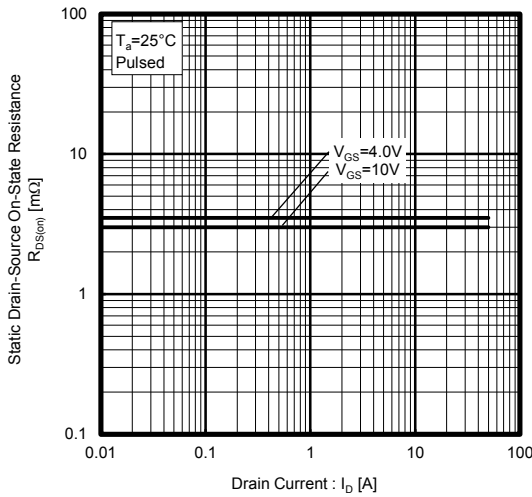


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

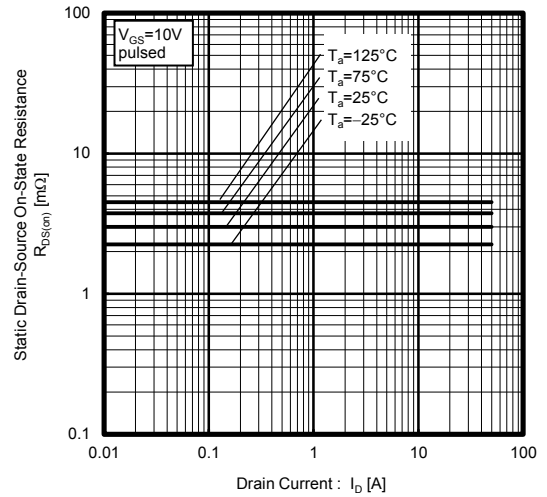


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

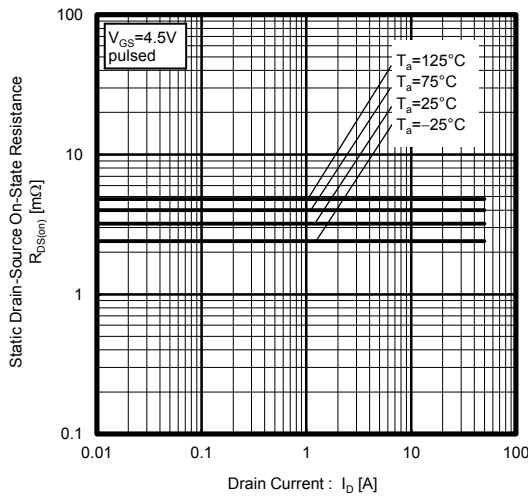


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

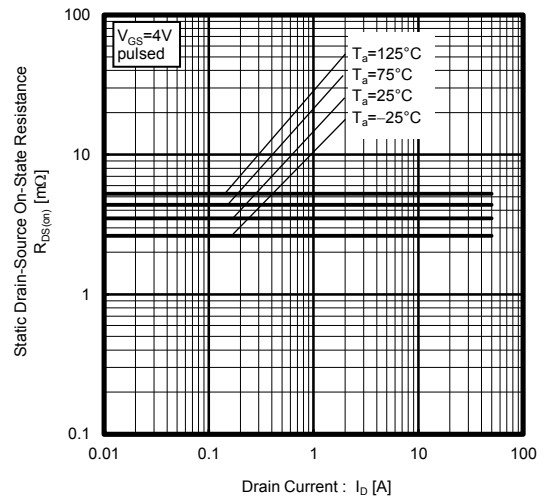


Fig.7 Forward Transfer Admittance vs. Drain Current

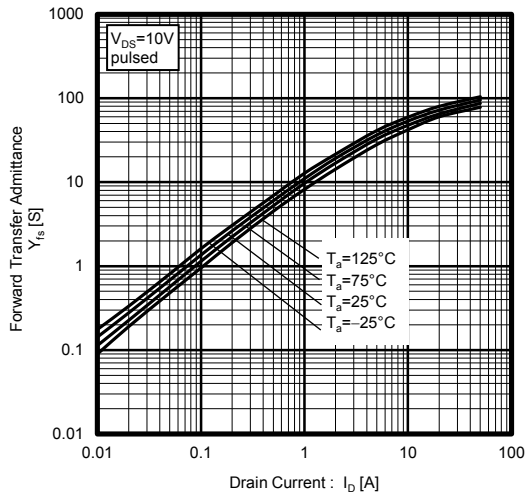


Fig.8 Typical Transfer Characteristics

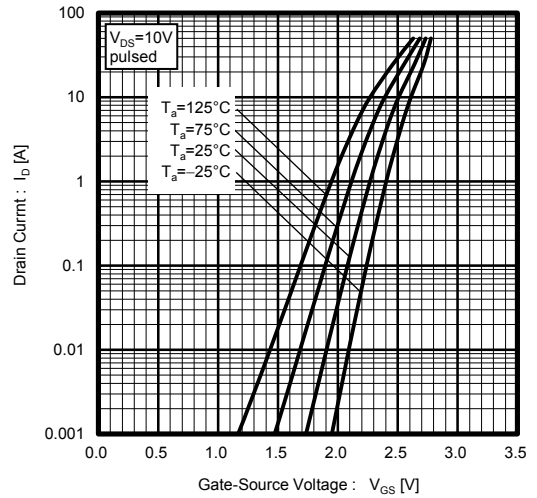


Fig.9 Source Current vs. Source-Drain Voltage

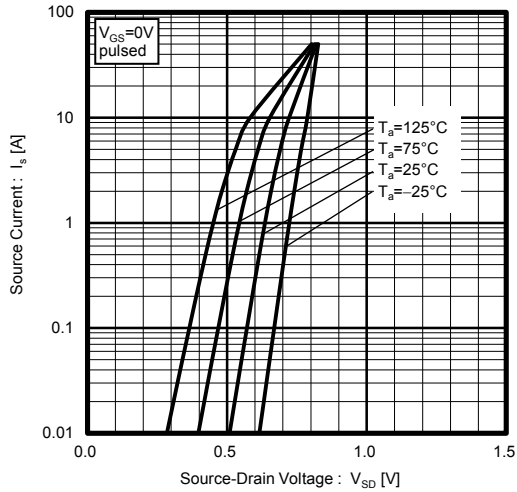


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

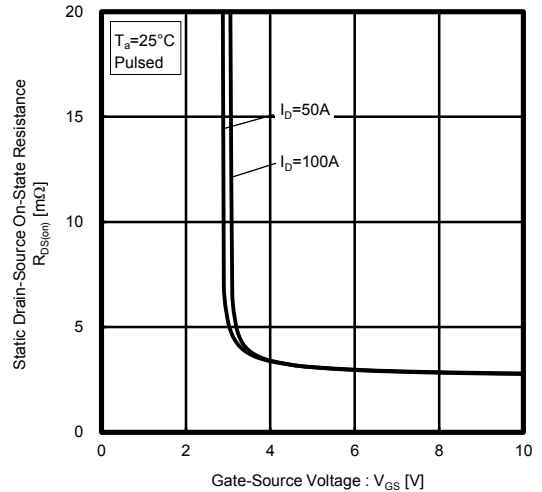


Fig.11 Switching Characteristics

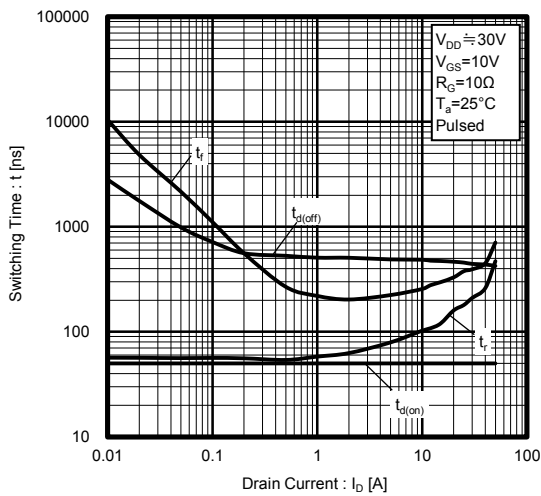


Fig.12 Dynamic Input Characteristics

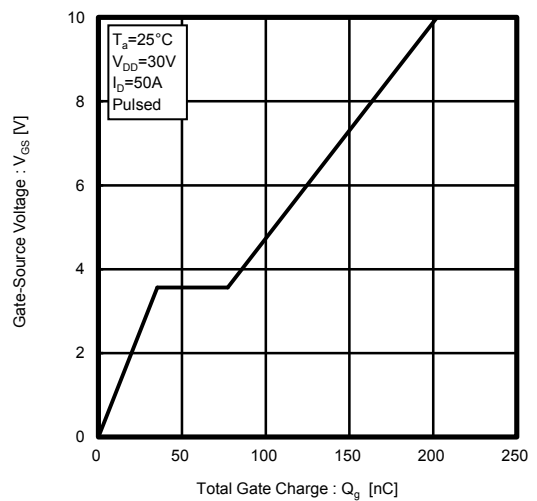


Fig.13 Typical Capacitance vs. Drain-Source Voltage

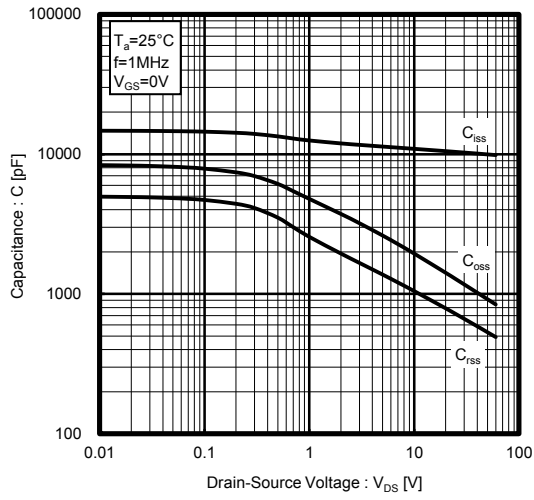
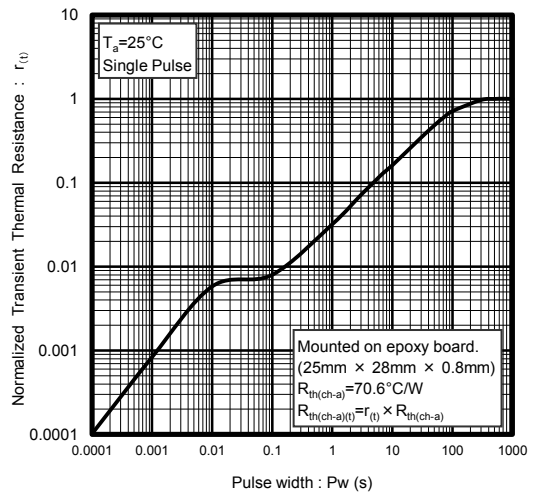


Fig.14 Normalized Transient Thermal Resistance v.s. Pulse Width



●Electrical characteristics (T<sub>a</sub> = 25°C)

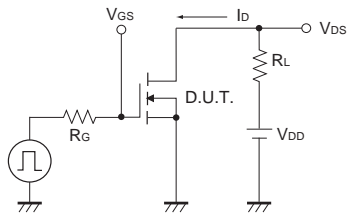


Fig.1-1 Switching Time Measurement Circuit

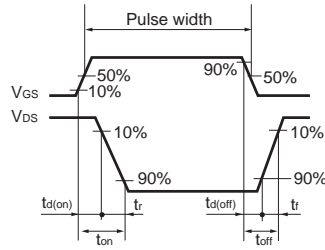


Fig.1-2 Switching Waveforms

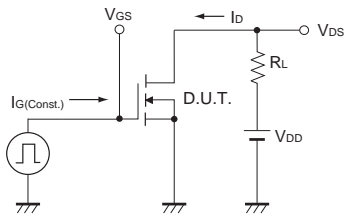


Fig.2-1 Gate Charge Measurement Circuit

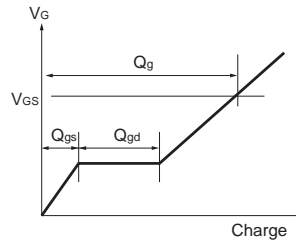


Fig.2-2 Gate Charge Waveform

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